

# **RFFM6205**

## 2.0V to 4.0V, 2.4GHz Front End Module

The RFFM6205 is a complete integrated solution in a single Front End Module (FEM) for Zigbee® applications in the 2.4GHz to 2.5GHz band and Bluetooth® transmitter applications. The ultra-small factor and integrated matching minimizes layout area in the customer's application and greatly reduces the number of external components. This simplifies the total front end solution by reducing the bill of materials, system footprint, and manufacturing cost.

The FEM integrates a power amplifier (PA) plus harmonic filter in the transmit (TX) path, a low noise amplifier (LNA) in the receive (RX) path, and a low loss bidirectional through mode path. The RFFM6205 incorporates two single-pole triple-throw (SP3T) switches to provide a single port for TDD access and a single antenna port for TX, RX, and through mode paths. The device is provided in a 2.5mm x 2.5mm x 0.5mm, 16-pin QFN package.



Functional Block Diagram

#### **Ordering Information**

RFFM6205SB	Standard 5 piece bag
RFFM6205SQ	Standard 25 piece bag
RFFM6205SR	Standard 100 piece reel
RFFM6205TR7	Standard 2500 piece reel
RFFM6205PCK-410	Fully assembled evaluation board w/5 pc bag

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## Package: QFN, 16-pin, 2.5mm x 2.5mm x 0.5mm

#### **Features**

- Tx Output Power = 14dBm
- Integrated RF Front End Module with Rx/Tx switch, PA, Filter, LNA, Bidirectional Thru path and 2-SP3T Switch
- 50Ω single-ended Bidirectional Transceiver Interface.
- Voltage Range = 2.0V to 4.0V
- Rx Noise Figure = 2.5dB

## **Applications**

- ZigBee® 802.15.4 Based Systems for Remote Monitoring and Control
- AA Battery Operation
- 2.4GHz ISM Band Applications
- Smart Meters for Energy Management
- Bluetooth® Transmitter systems

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## **Absolute Maximum Ratings**

Parameter	Rating	Unit
Voltage	4.5	V
Operating Temperature	-40 to +125	°C
Storage Temperature	-40 to +150	°C
Maximum Input Power to PA	+20	dBm
Maximum Input Power to LNA	+5	dBm
ESD, HBM (Pin-to-GND)	500	V
ESD, CDM (Pin-to-GND)	500	V
Moisture Sensitivity	MSL 3	



**∂** rfmd⋙ RFMD Green: RoHS status based on EU Directive 2011/65/EU (at time of this document revision), halogen free per IEC 61249-2-21, < 1000ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in solder.

Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

## **Nominal Operating Parameters**

Parameter	Specification			Unit	Condition
raiailletei	Min	Тур	Max	Onit	Condition
					Specifications must be met across supply voltage, control voltage, and temperature ranges unless otherwise specified
TX Frequency	2405		2485	MHz	
RX Frequency	2405		2485	MHz	
Bypass Frequency	2405		2485	MHz	
ANT RF Port Impedance		50		Ω	
RFIO Port Impedance		50		Ω	
V <sub>BAT</sub>	2.0	3.0	4.0	V	
Off Mode Current - Leakage					V <sub>DD</sub> _TX = 3.0V, C_EN = Low, V <sub>DD</sub> _RX = 3.0V, C_TX = Low, C_RX = Low, C_BYP = Low, Temp =25°C
Supply Current - IDDTX		50	200	nA	
Supply Current - IDDRX		50	200	nA	
C_RX Current			1.0	nA	
C_TX Current			1.0	nA	
C_BYP Current			1.0	nA	
Transmit Mode - Power Amplifier					V <sub>DD</sub> _TX = 3.0V, C_EN = High, V <sub>DD</sub> _RX = 3.0V, C_TX =High, C_RX =Low, C_BYP =Low, Temp =25°C unless otherwise specified
Input Return Loss			10.0	dB	
Output Return Loss			8.0	dB	
Small Signal Gain	11.0	14.0		dB	
Gain Flatness	-0.3		0.3	dB	
Rated Output Power		15.0		dBm	VDD_TX = 4.0V
	13.0	14.0		dBm	VDD_TX = 3.3V
	12.5	13.5		dBm	VDD_TX = 3.0V
	10.0	11.0		dBm	VDD_TX = 2.0V

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## **RFFM6205**



Bauanatan	Specification			Unit		
	Min	Тур	Max	Unit	Condition	
Transmit Mode - Power Amplifier (continued)					V <sub>DD</sub> _TX = 3.0V, C_EN = High, V <sub>DD</sub> _RX = 3.0V, C_TX =High, C_RX =Low, C_BYP =Low, Temp =25°C	
Supply Current		13	18	mA	VDD_TX = 2.0V; P <sub>OUT</sub> = 10dBm	
		17	21	mA	VDD TX = 3.0V: Pour = 13dBm	
		19	23	mΑ	$VDD_TX = 3.3V$ : Pour = 14dBm	
		21	27	mΑ	VDD_TX = 4.0V; Pour = 15dBm	
Quiescent Current		5	21	mΔ		
$2f0: P_{our} = 14dBm$		-20.0	-15.0	dBm/MHz		
$2f0$ ; $P_{OUT} = 14dBm$ , with external filter		-45.0	-42.0	dBm/MHz		
$3f0: P_{OUT} = 14dBm$		-50.0		dBm/MHz		
VSWR: Stability (ruggedness)			4:1			
VSWR: No Damage			8:1			
Gain Settling Time		230	300	ns	10% to 90%	
Receive Mode – LNA					V <sub>DD</sub> _TX = 3.0V, C_EN = High, V <sub>DD</sub> _RX = 3.0V, C_TX =Low, C_RX =High, C_BYP =Low, Temp =25°C	
Input Return Loss		12.0	9.0	dB		
Output Return Loss		10.0	8.0	dB		
Gain	11.0	14.0	14.5	dB		
Gain Flatness	-0.3		0.3	dB		
Noise Figure		2.5	3.0	dB		
Supply Current	2.0	4.0	7.0	mA		
IIP3		4.0		dBm		
IP1dB	-8.0	-5.0		dBm		
Bidirectional Thru Mode					V <sub>DD</sub> _TX = 3.0V, C_EN = High, V <sub>DD</sub> _RX = 3.0V, C_TX =Low, C_RX =Low, C_BYP =High, Temp =25°C	
Insertion Loss		1.5	2.5	dB		
Input Return Loss			10.0	dB		
Output Return Loss			10.0	dB		
Supply Current		100	400	nA		
IIP3	35.0	40.0		dBm		
Gain flatness	-0.3		0.3	dB		
Maximum Input Power	25			dBm		
Bluetooth Transmitter GFSK						
20dB Bandwidth		870		kHz		
Adjacent Channel Power $ M - N  = 2$		-63		dBc		
Adjacent Channel Power $ M - N  \ge 3$		-72		dBc		
Bluetooth Transmitter EDR						
In-Band Spurious Emission		-35		dBc		
Adjacent Channel Power  M – N  = 2		-33		dBc		
Adjacent Channel Power $ M - N  \ge 3$		-45		dBc		
Logic						
Logic Level "High"	1.6	1.8	VBAT	V		

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Parameter	Specification			Unit	Condition
T di di licitori	Min	Тур	Max	Onit	Condition
Logic					
Logic Level "Low"	0.0		0.2	V	
C_TX Input source current at Logic "High"		100	800	μA	
C_RX Input source current at Logic "High"		100	600	uA	
C_BYP Input source current at Logic "High"		0.1	1.0	uA	
C_EN Input source current at Logic "High"			3.0	uA	
Input source current Logic Level "Low"			0.001	μA	

## Switch Control Logic Table

Mode	C_EN	C_TX	C_RX	C_BYP
TX Mode	High	High	Low	Low
RX Mode	High	Low	High	Low
Bypass Mode	High	Low	Low	High
Power Down	Low	Low	Low	Low



## **Application Schematic**





### **Pin Out**



## Package Outline and Branding Drawing (Dimensions in millimeters)



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## **Recommended PCB Patterns**





## **Pin Names and Descriptions**

Pin	Name	Description			
1	C_TX	Control Pin: Transmit Enable/Disable, view logic table for operation			
2	N/C	No Internal Connection; Open on PCB			
3	GND	No Internal Connection; Ground on PCB			
4	RF I/O	RF Input/Output signal: internally matched to 50 $\Omega$ , DC Blocked			
5	GND	No Internal Connection; Ground on PCB			
6	VDD_RX	Receive Low Noise Amplifier Voltage Supply			
7	GND	No Internal Connection; Ground on PCB			
8	N/C	No Internal Connection; No Connect on PCB			
9	N/C	No Internal Connection; No Connect on PCB			
10	GND	No Internal Connection; Ground on PCB			
11	ANT	Antenna Switch Common Port, internally matched to 50 ohms, DC Blocked			
12	GND	No Internal Connection; Ground on PCB			
13	VDD_TX	Transmit Power Amplifier Voltage Supply			
14	C_EN	Control Pin: Enable FEM, view logic table for operation			
15	C_BYP	Control Pin: Bypass Enable/Disable, view logic table for operation			
16	C_RX	Control Pin: Receive Enable/Disable, view logic table for operation			
Pkg Base	GND	Ground connection. The back side of the package should be connected to the ground plane through as short a connection as possible, e.g., PCB vias under the device are recommended.			